

FIG.1

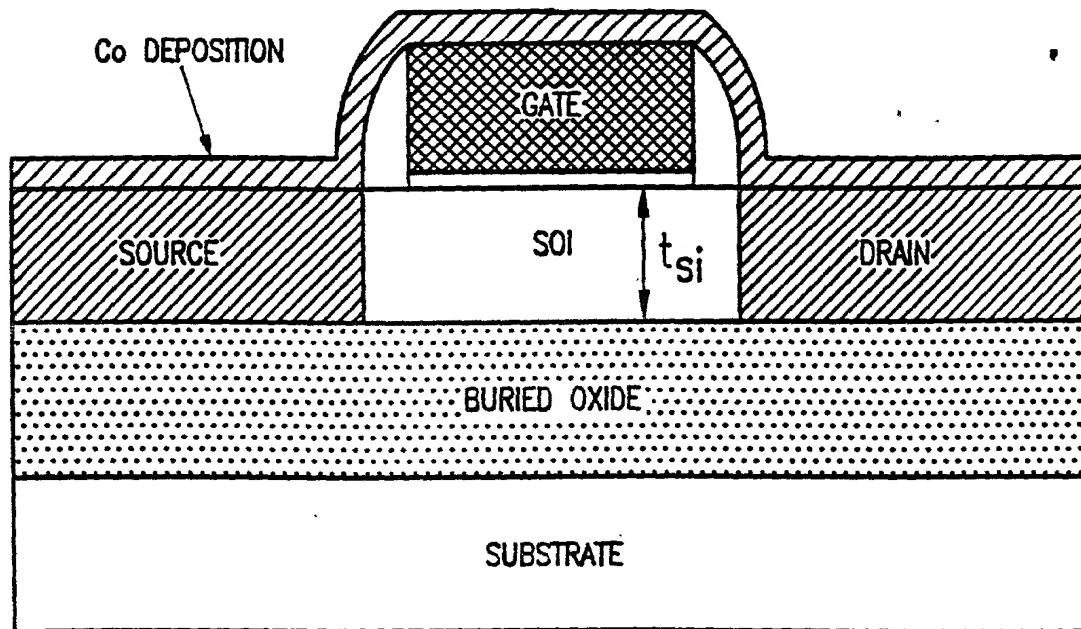


FIG.2

FORM  $\text{Co}_2\text{Si}$  BY LOW TEMPERATURE ANNEAL

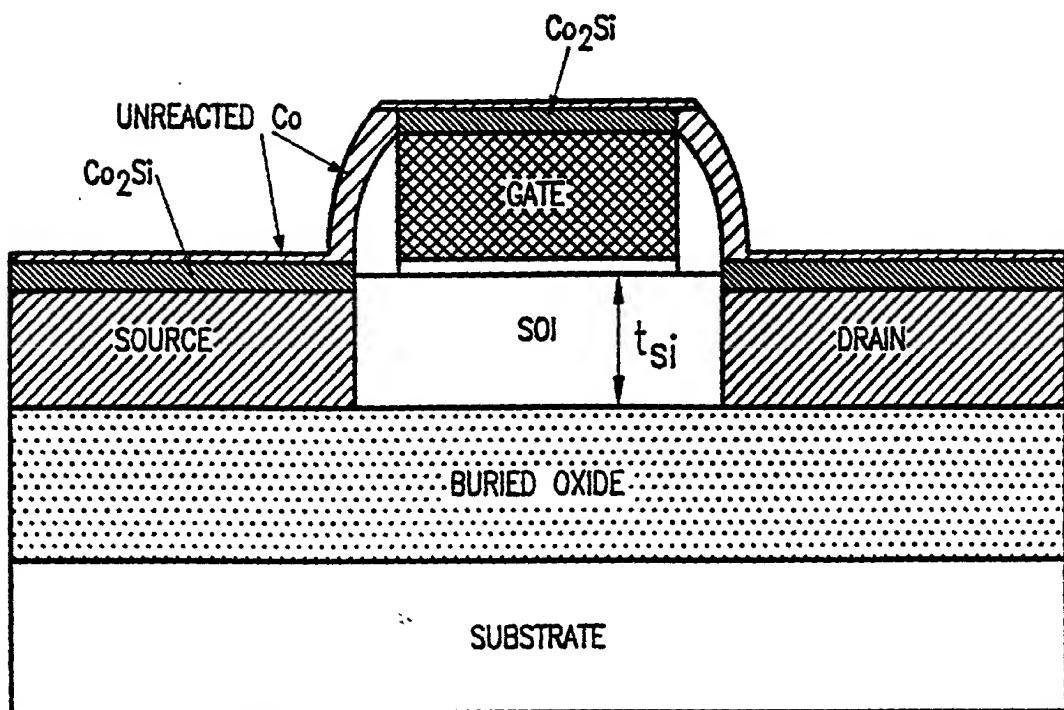


FIG.3

DEPOSITE  $\text{a-Si}$

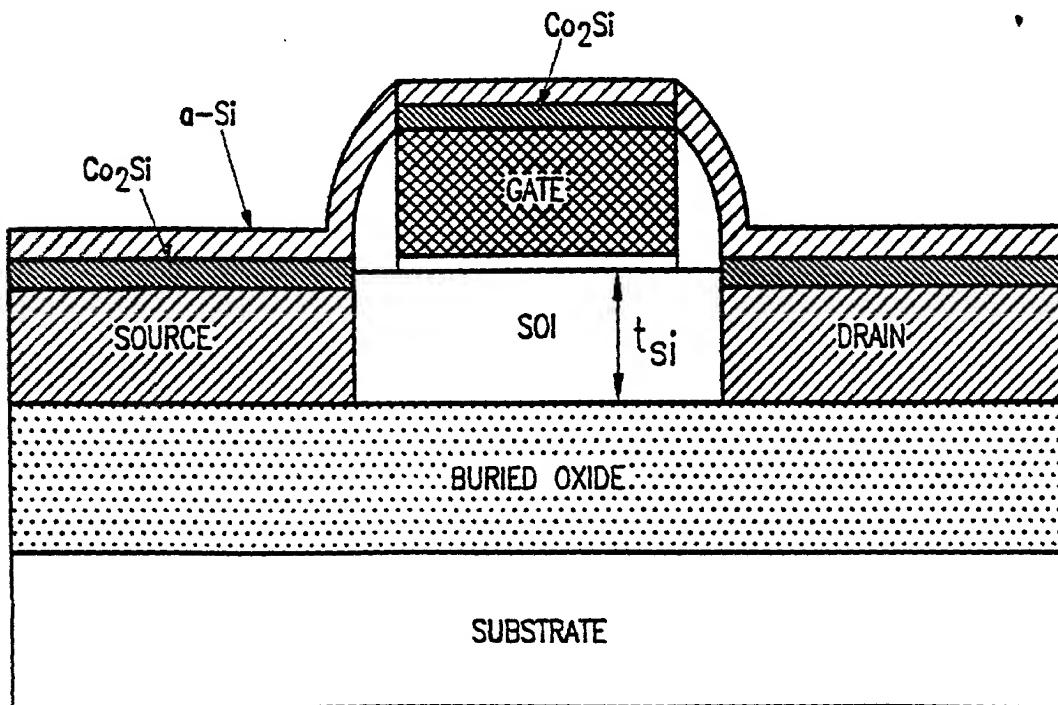


FIG.4

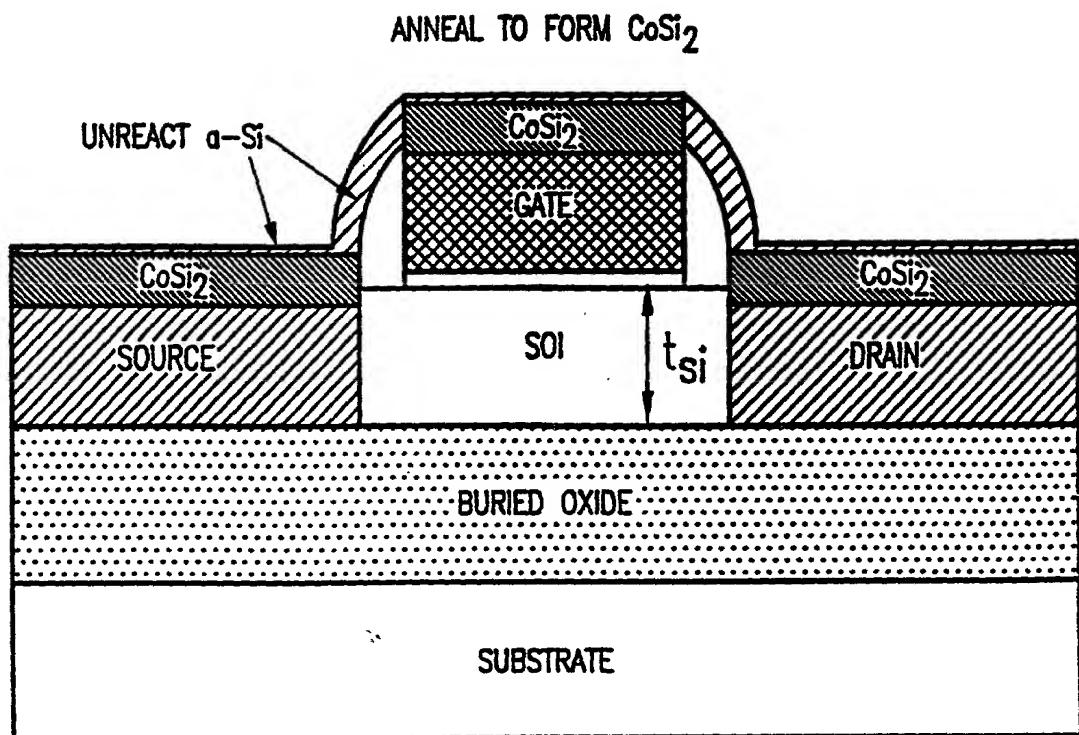


FIG.5

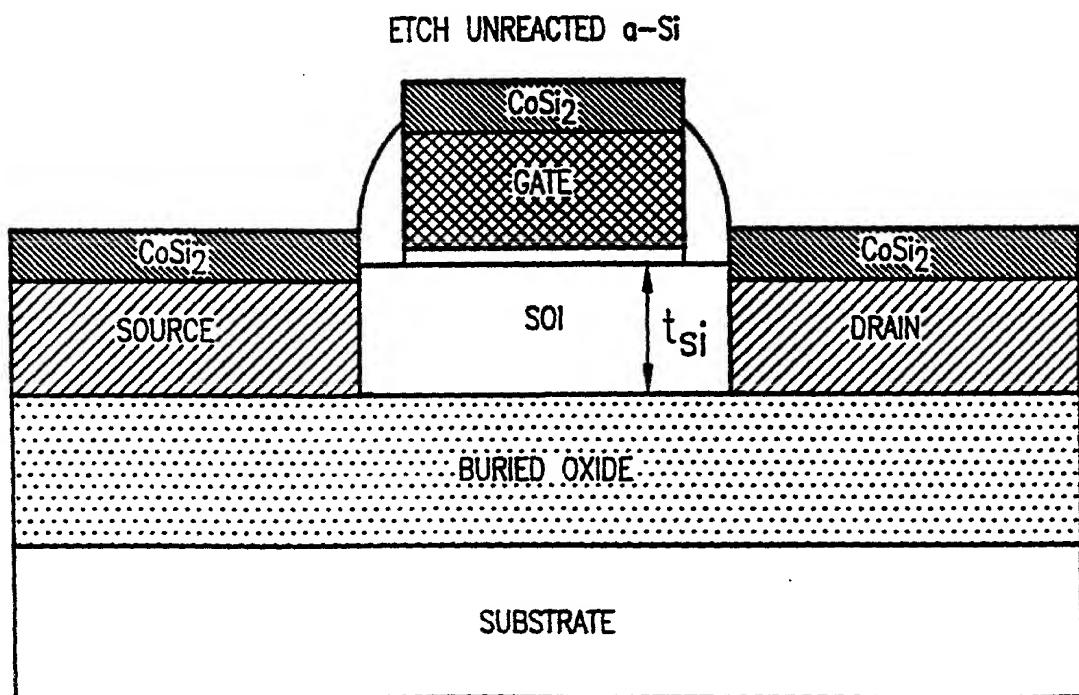
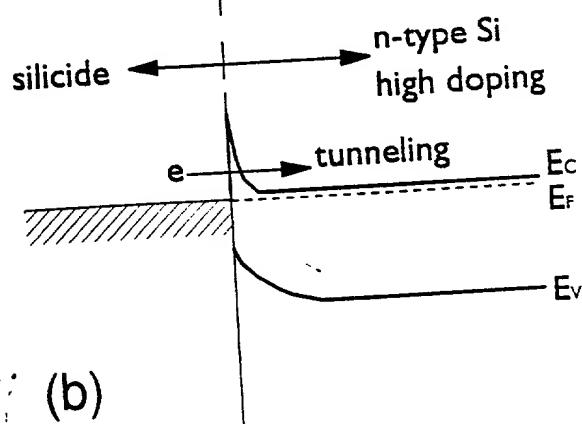
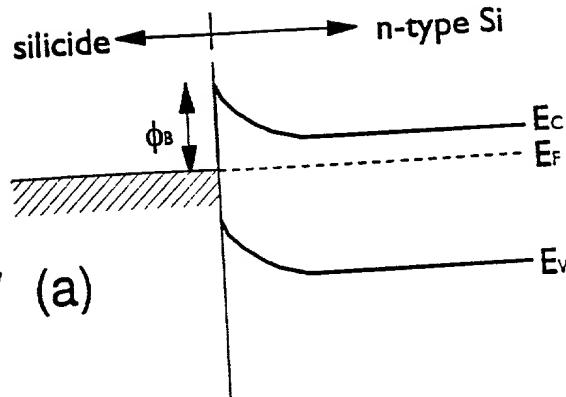
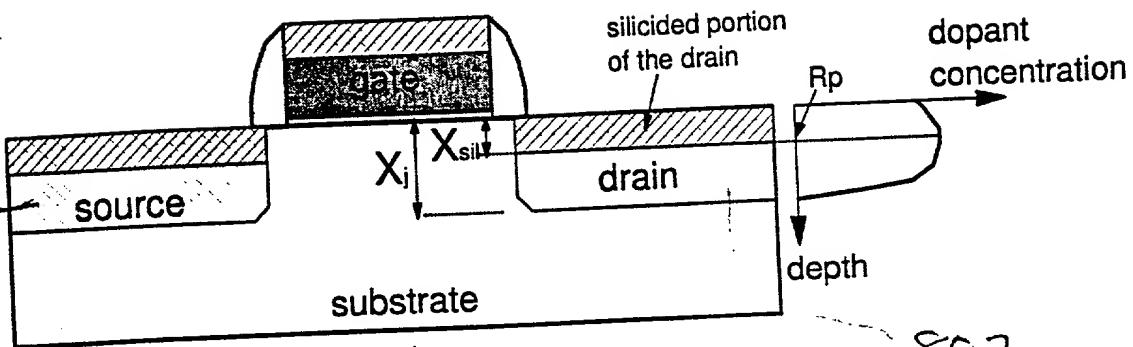


FIG.6





$X_j$  = source or drain junction depth

$X_{sil}$  = silicide junction depth

$R_p$  = peak dopant concentration

Requirements:

1.  $X_j > X_{sil}$
2.  $X_{sil}$  roughly equals  $R_p$

Figure 8

